



Welcome to [E-XFL.COM](https://www.e-xfl.com)

What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	80MHz
Connectivity	CANbus, EBI/EMI, I ² C, IrDA, LINbus, MMC/SD, QSPI, SAI, SPI, SWPMI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, LCD, PWM, WDT
Number of I/O	114
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	128K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 24x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	144-LQFP
Supplier Device Package	144-LQFP (20x20)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l476zgt6

Table 2. STM32L476xx family device features and peripheral counts (continued)

Peripheral	STM32L476 Zx	STM32L476 Qx	STM32L476 Vx	STM32L476 Mx	STM32L476 Jx	STM32L476 Rx
Max. CPU frequency	80 MHz					
Operating voltage	1.71 to 3.6 V					
Operating temperature	Ambient operating temperature: -40 to 85 °C / -40 to 105 °C / -40 to 125 °C Junction temperature: -40 to 105 °C / -40 to 125 °C / -40 to 130 °C					
Packages	LQFP144	UFBGA132	LQFP100	WLCSP81	WLCSP72	LQFP64

1. For the LQFP100 package, only FMC Bank1 is available. Bank1 can only support a multiplexed NOR/PSRAM memory using the NE1 Chip Select.

3.4 Embedded Flash memory

STM32L476xx devices feature up to 1 Mbyte of embedded Flash memory available for storing programs and data. The Flash memory is divided into two banks allowing read-while-write operations. This feature allows to perform a read operation from one bank while an erase or program operation is performed to the other bank. The dual bank boot is also supported. Each bank contains 256 pages of 2 Kbyte.

Flexible protections can be configured thanks to option bytes:

- Readout protection (RDP) to protect the whole memory. Three levels are available:
 - Level 0: no readout protection
 - Level 1: memory readout protection: the Flash memory cannot be read from or written to if either debug features are connected, boot in RAM or bootloader is selected
 - Level 2: chip readout protection: debug features (Cortex-M4 JTAG and serial wire), boot in RAM and bootloader selection are disabled (JTAG fuse). This selection is irreversible.

Table 3. Access status versus readout protection level and execution modes

Area	Protection level	User execution			Debug, boot from RAM or boot from system memory (loader)		
		Read	Write	Erase	Read	Write	Erase
Main memory	1	Yes	Yes	Yes	No	No	No
	2	Yes	Yes	Yes	N/A	N/A	N/A
System memory	1	Yes	No	No	Yes	No	No
	2	Yes	No	No	N/A	N/A	N/A
Option bytes	1	Yes	Yes	Yes	Yes	Yes	Yes
	2	Yes	No	No	N/A	N/A	N/A
Backup registers	1	Yes	Yes	N/A ⁽¹⁾	No	No	N/A ⁽¹⁾
	2	Yes	Yes	N/A	N/A	N/A	N/A
SRAM2	1	Yes	Yes	Yes ⁽¹⁾	No	No	No ⁽¹⁾
	2	Yes	Yes	Yes	N/A	N/A	N/A

1. Erased when RDP change from Level 1 to Level 0.

- Write protection (WRP): the protected area is protected against erasing and programming. Two areas per bank can be selected, with 2-Kbyte granularity.
- Proprietary code readout protection (PCROP): a part of the flash memory can be protected against read and write from third parties. The protected area is execute-only: it can only be reached by the STM32 CPU, as an instruction code, while all other accesses (DMA, debug and CPU data read, write and erase) are strictly prohibited. One area per bank can be selected, with 64-bit granularity. An additional option bit (PCROP_RDP) allows to select if the PCROP area is erased or not when the RDP protection is changed from Level 1 to Level 0.

Standby mode, supplied by the low-power Regulator (Standby with RAM2 retention mode).

The device exits Standby mode when an external reset (NRST pin), an IWDG reset, WKUP pin event (configurable rising or falling edge), or an RTC event occurs (alarm, periodic wakeup, timestamp, tamper) or a failure is detected on LSE (CSS on LSE).

The system clock after wakeup is MSI up to 8 MHz.

- **Shutdown mode**

The Shutdown mode allows to achieve the lowest power consumption. The internal regulator is switched off so that the VCORE domain is powered off. The PLL, the HSI16, the MSI, the LSI and the HSE oscillators are also switched off.

The RTC can remain active (Shutdown mode with RTC, Shutdown mode without RTC).

The BOR is not available in Shutdown mode. No power voltage monitoring is possible in this mode, therefore the switch to Backup domain is not supported.

SRAM1, SRAM2 and register contents are lost except for registers in the Backup domain.

The device exits Shutdown mode when an external reset (NRST pin), a WKUP pin event (configurable rising or falling edge), or an RTC event occurs (alarm, periodic wakeup, timestamp, tamper).

The system clock after wakeup is MSI at 4 MHz.

3.10 Interconnect matrix

Several peripherals have direct connections between them. This allows autonomous communication between peripherals, saving CPU resources thus power supply consumption. In addition, these hardware connections allow fast and predictable latency.

Depending on peripherals, these interconnections can operate in Run, Sleep, low-power run and sleep, Stop 0, Stop 1 and Stop 2 modes.

Table 6. STM32L476xx peripherals interconnect matrix

Interconnect source	Interconnect destination	Interconnect action	Run	Sleep	Low-power run	Low-power sleep	Stop 0 / Stop 1	Stop 2
TIMx	TIMx	Timers synchronization or chaining	Y	Y	Y	Y	-	-
	ADCx DACx DFSDM	Conversion triggers	Y	Y	Y	Y	-	-
	DMA	Memory to memory transfer trigger	Y	Y	Y	Y	-	-
	COMPx	Comparator output blanking	Y	Y	Y	Y	-	-
COMPx	TIM1, 8 TIM2, 3	Timer input channel, trigger, break from analog signals comparison	Y	Y	Y	Y	-	-
	LPTIMERx	Low-power timer triggered by analog signals comparison	Y	Y	Y	Y	Y	Y ⁽¹⁾
ADCx	TIM1, 8	Timer triggered by analog watchdog	Y	Y	Y	Y	-	-
RTC	TIM16	Timer input channel from RTC events	Y	Y	Y	Y	-	-
	LPTIMERx	Low-power timer triggered by RTC alarms or tampers	Y	Y	Y	Y	Y	Y ⁽¹⁾
All clocks sources (internal and external)	TIM2 TIM15, 16, 17	Clock source used as input channel for RC measurement and trimming	Y	Y	Y	Y	-	-
USB	TIM2	Timer triggered by USB SOF	Y	Y	-	-	-	-
CSS CPU (hard fault) RAM (parity error) Flash memory (ECC error) COMPx PVD DFSDM (analog watchdog, short circuit detection)	TIM1,8 TIM15,16,17	Timer break	Y	Y	Y	Y	-	-

3.15 Analog to digital converter (ADC)

The device embeds 3 successive approximation analog-to-digital converters with the following features:

- 12-bit native resolution, with built-in calibration
- 5.33 Msps maximum conversion rate with full resolution
 - Down to 18.75 ns sampling time
 - Increased conversion rate for lower resolution (up to 8.88 Msps for 6-bit resolution)
- Up to 24 external channels, some of them shared between ADC1 and ADC2, or ADC1, ADC2 and ADC3.
- 5 Internal channels: internal reference voltage, temperature sensor, VBAT/3, DAC1 and DAC2 outputs.
- One external reference pin is available on some package, allowing the input voltage range to be independent from the power supply
- Single-ended and differential mode inputs
- Low-power design
 - Capable of low-current operation at low conversion rate (consumption decreases linearly with speed)
 - Dual clock domain architecture: ADC speed independent from CPU frequency
- Highly versatile digital interface
 - Single-shot or continuous/discontinuous sequencer-based scan mode: 2 groups of analog signals conversions can be programmed to differentiate background and high-priority real-time conversions
 - Handles two ADC converters for dual mode operation (simultaneous or interleaved sampling modes)
 - Each ADC support multiple trigger inputs for synchronization with on-chip timers and external signals
 - Results stored into 3 data register or in RAM with DMA controller support
 - Data pre-processing: left/right alignment and per channel offset compensation
 - Built-in oversampling unit for enhanced SNR
 - Channel-wise programmable sampling time
 - Three analog watchdog for automatic voltage monitoring, generating interrupts and trigger for selected timers
 - Hardware assistant to prepare the context of the injected channels to allow fast context switching

3.15.1 Temperature sensor

The temperature sensor (TS) generates a voltage V_{TS} that varies linearly with temperature.

The temperature sensor is internally connected to the ADC1_IN17 and ADC3_IN17 input channels which is used to convert the sensor output voltage into a digital value.

The sensor provides good linearity but it has to be calibrated to obtain good overall accuracy of the temperature measurement. As the offset of the temperature sensor varies from chip to chip due to process variation, the uncalibrated internal temperature sensor is suitable for applications that detect temperature changes only.

3.28 Low-power universal asynchronous receiver transmitter (LPUART)

The device embeds one Low-Power UART. The LPUART supports asynchronous serial communication with minimum power consumption. It supports half duplex single wire communication and modem operations (CTS/RTS). It allows multiprocessor communication.

The LPUART has a clock domain independent from the CPU clock, and can wakeup the system from Stop mode. The wake up events from Stop mode are programmable and can be:

- Start bit detection
- Any received data frame
- A specific programmed data frame

Only a 32.768 kHz clock (LSE) is needed to allow LPUART communication up to 9600 baud. Therefore, even in Stop mode, the LPUART can wait for an incoming frame while having an extremely low energy consumption. Higher speed clock can be used to reach higher baudrates.

LPUART interface can be served by the DMA controller.

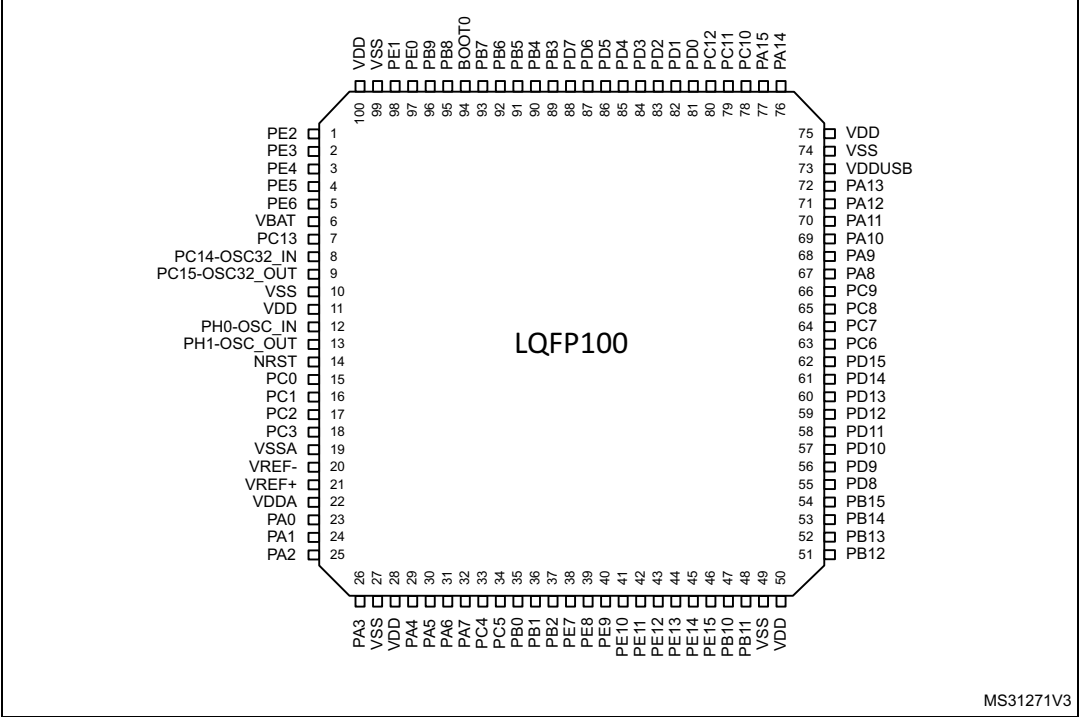
Figure 5. STM32L476Qx UFBGA132 ballout⁽¹⁾

	1	2	3	4	5	6	7	8	9	10	11	12				
A	PE3	PE1	PB8	BOOT0	PD7	PD5	PB4	PB3	PA15	PA14	PA13	PA12				
B	PE4	PE2	PB9	PB7	PB6	PD6	PD4	PD3	PD1	PC12	PC10	PA11				
C	PC13	PE5	PE0	VDD	PB5	PG14	PG13	PD2	PD0	PC11	VDDUSB	PA10				
D	PC14-OSC32_IN	PE6	VSS	PF2	PF1	PF0	PG12	PG10	PG9	PA9	PA8	PC9				
E	PC15-OSC32_OUT	VBAT	VSS	PF3	<table><tr><td>VSS</td><td>VSS</td></tr><tr><td>VDD</td><td>VDDIO2</td></tr></table>				VSS	VSS	VDD	VDDIO2	PG5	PC8	PC7	PC6
VSS	VSS															
VDD	VDDIO2															
F	PH0-OSC_IN	VSS	PF4	PF5	PG3	PG4	VSS	VSS								
G	PH1-OSC_OUT	VDD	PG11	PG6					PG1	PG2	VDD	VDD				
H	PC0	NRST	VDD	PG7					PG0	PD15	PD14	PD13				
J	VSSA/VREF-	PC1	PC2	PA4	PA7	PG8	PF12	PF14	PF15	PD12	PD11	PD10				
K	PG15	PC3	PA2	PA5	PC4	PF11	PF13	PD9	PD8	PB15	PB14	PB13				
L	VREF+	PA0	PA3	PA6	PC5	PB2	PE8	PE10	PE12	PB10	PB11	PB12				
M	VDDA	PA1	OPAMP1_VINM	OPAMP2_VINM	PB0	PB1	PE7	PE9	PE11	PE13	PE14	PE15				

MSV35003V7

1. The above figure shows the package top view.

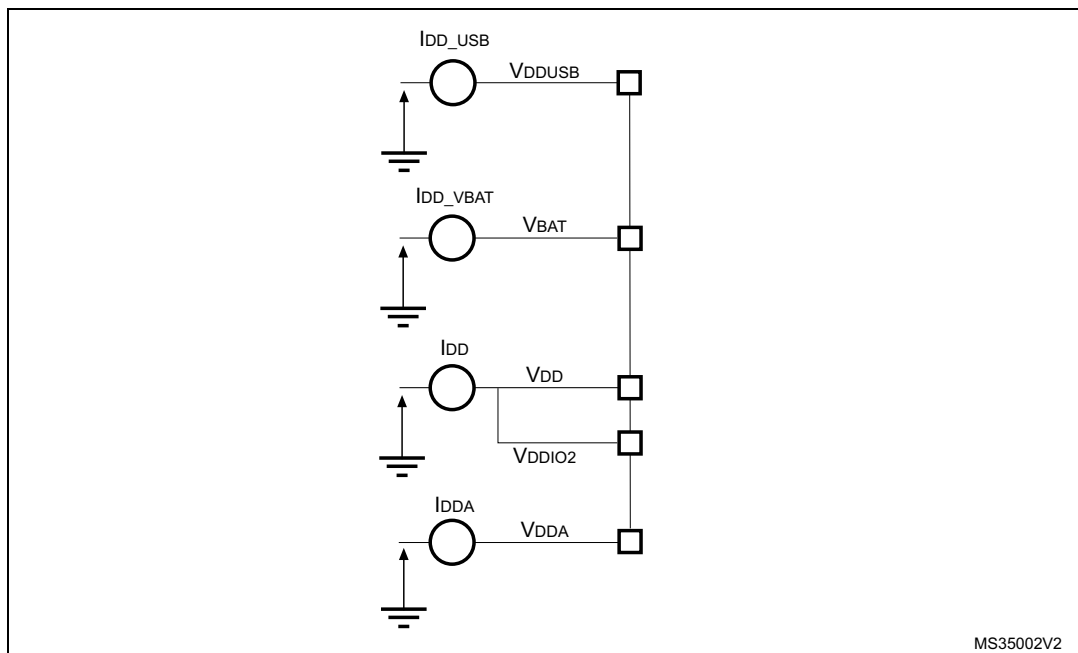
Figure 6. STM32L476Vx LQFP100 pinout⁽¹⁾



1. The above figure shows the package top view.

6.1.7 Current consumption measurement

Figure 14. Current consumption measurement scheme



6.2 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in [Table 19: Voltage characteristics](#), [Table 20: Current characteristics](#) and [Table 21: Thermal characteristics](#) may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Table 19. Voltage characteristics⁽¹⁾

Symbol	Ratings	Min	Max	Unit
$V_{DDX} - V_{SS}$	External main supply voltage (including V_{DD} , V_{DDA} , V_{DDIO2} , V_{DDUSB} , V_{LCD} , V_{BAT})	-0.3	4.0	V
$V_{IN}^{(2)}$	Input voltage on FT_XXX pins	$V_{SS}-0.3$	$\min(V_{DD}, V_{DDA}, V_{DDIO2}, V_{DDUSB}, V_{LCD}) + 4.0^{(3)(4)}$	V
	Input voltage on TT_XX pins	$V_{SS}-0.3$	4.0	
	Input voltage on BOOT0 pin	V_{SS}	9.0	
	Input voltage on any other pins	$V_{SS}-0.3$	4.0	
$ \Delta V_{DDx} $	Variations between different V_{DDx} power pins of the same domain	-	50	mV
$ V_{SSx}-V_{SS} $	Variations between all the different ground pins ⁽⁵⁾	-	50	mV

1. All main power (V_{DD} , V_{DDA} , V_{DDIO2} , V_{DDUSB} , V_{LCD} , V_{BAT}) and ground (V_{SS} , V_{SSA}) pins must always be connected to the external power supply, in the permitted range.

I/O system current consumption

The current consumption of the I/O system has two components: static and dynamic.

I/O static current consumption

All the I/Os used as inputs with pull-up generate current consumption when the pin is externally held low. The value of this current consumption can be simply computed by using the pull-up/pull-down resistors values given in [Table 58: I/O static characteristics](#).

For the output pins, any external pull-down or external load must also be considered to estimate the current consumption.

Additional I/O current consumption is due to I/Os configured as inputs if an intermediate voltage level is externally applied. This current consumption is caused by the input Schmitt trigger circuits used to discriminate the input value. Unless this specific configuration is required by the application, this supply current consumption can be avoided by configuring these I/Os in analog mode. This is notably the case of ADC input pins which should be configured as analog inputs.

Caution: Any floating input pin can also settle to an intermediate voltage level or switch inadvertently, as a result of external electromagnetic noise. To avoid current consumption related to floating pins, they must either be configured in analog mode, or forced internally to a definite digital value. This can be done either by using pull-up/down resistors or by configuring the pins in output mode.

I/O dynamic current consumption

In addition to the internal peripheral current consumption measured previously (see [Table 40: Peripheral current consumption](#)), the I/Os used by an application also contribute to the current consumption. When an I/O pin switches, it uses the current from the I/O supply voltage to supply the I/O pin circuitry and to charge/discharge the capacitive load (internal or external) connected to the pin:

$$I_{SW} = V_{DDIOx} \times f_{SW} \times C$$

where

I_{SW} is the current sunk by a switching I/O to charge/discharge the capacitive load

V_{DDIOx} is the I/O supply voltage

f_{SW} is the I/O switching frequency

C is the total capacitance seen by the I/O pin: $C = C_{INT} + C_{EXT} + C_S$

C_S is the PCB board capacitance including the pad pin.

The test pin is configured in push-pull output mode and is toggled by software at a fixed frequency.

On-chip peripheral current consumption

The current consumption of the on-chip peripherals is given in [Table 40](#). The MCU is placed under the following conditions:

- All I/O pins are in Analog mode
- The given value is calculated by measuring the difference of the current consumptions:
 - when the peripheral is clocked on
 - when the peripheral is clocked off
- Ambient operating temperature and supply voltage conditions summarized in [Table 19: Voltage characteristics](#)
- The power consumption of the digital part of the on-chip peripherals is given in [Table 40](#). The power consumption of the analog part of the peripherals (where applicable) is indicated in each related section of the datasheet.

Table 40. Peripheral current consumption

Peripheral		Range 1	Range 2	Low-power run and sleep	Unit
AHB	Bus Matrix ⁽¹⁾	4.5	3.7	4.1	μA/MHz
	ADC independent clock domain	0.4	0.1	0.2	
	ADC AHB clock domain	5.5	4.7	5.5	
	CRC	0.4	0.2	0.3	
	DMA1	1.4	1.3	1.4	
	DMA2	1.5	1.3	1.4	
	FLASH	6.2	5.2	5.8	
	FMC	8.9	7.5	8.4	
	GPIOA ⁽²⁾	4.8	3.8	4.4	
	GPIOB ⁽²⁾	4.8	4.0	4.6	
	GPIOC ⁽²⁾	4.5	3.8	4.3	
	GPIOD ⁽²⁾	4.6	3.9	4.4	
	GPIOE ⁽²⁾	5.2	4.5	4.9	
	GPIOF ⁽²⁾	5.9	4.9	5.7	
	GPIOG ⁽²⁾	4.3	3.8	4.2	
	GPIOH ⁽²⁾	0.7	0.6	0.8	
	OTG_FS independent clock domain	23.2	NA	NA	
	OTG_FS AHB clock domain	16.4	NA	NA	
	QUADSPI	7.8	6.7	7.3	
	RNG independent clock domain	2.2	NA	NA	
	RNG AHB clock domain	0.6	NA	NA	
	SRAM1	0.9	0.8	0.9	

Table 50. PLL, PLLSAI1, PLLSAI2 characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$f_{\text{PLL_IN}}$	PLL input clock ⁽²⁾	-	4	-	16	MHz
	PLL input clock duty cycle	-	45	-	55	%
$f_{\text{PLL_P_OUT}}$	PLL multiplier output clock P	Voltage scaling Range 1	2.0645	-	80	MHz
		Voltage scaling Range 2	2.0645	-	26	
$f_{\text{PLL_Q_OUT}}$	PLL multiplier output clock Q	Voltage scaling Range 1	8	-	80	MHz
		Voltage scaling Range 2	8	-	26	
$f_{\text{PLL_R_OUT}}$	PLL multiplier output clock R	Voltage scaling Range 1	8	-	80	MHz
		Voltage scaling Range 2	8	-	26	
$f_{\text{VCO_OUT}}$	PLL VCO output	Voltage scaling Range 1	64	-	344	MHz
		Voltage scaling Range 2	64	-	128	
t_{LOCK}	PLL lock time	-	-	15	40	μs
Jitter	RMS cycle-to-cycle jitter	System clock 80 MHz	-	40	-	$\pm\text{ps}$
	RMS period jitter		-	30	-	
$I_{\text{DD}}(\text{PLL})$	PLL power consumption on V_{DD} ⁽¹⁾	VCO freq = 64 MHz	-	150	200	μA
		VCO freq = 96 MHz	-	200	260	
		VCO freq = 192 MHz	-	300	380	
		VCO freq = 344 MHz	-	520	650	

1. Guaranteed by design.

2. Take care of using the appropriate division factor M to obtain the specified PLL input clock values. The M factor is shared between the 3 PLLs.

Table 58. I/O static characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{lkg}	FT_xx input leakage current ⁽³⁾	$V_{IN} \leq \text{Max}(V_{DDXXX})^{(4)}$	-	-	± 100	nA
		$\text{Max}(V_{DDXXX}) \leq V_{IN} \leq \text{Max}(V_{DDXXX}) + 1 \text{ V}^{(4)(5)}$	-	-	$650^{(3)(6)}$	
		$\text{Max}(V_{DDXXX}) + 1 \text{ V} < V_{IN} \leq 5.5 \text{ V}^{(3)(5)}$	-	-	$200^{(6)}$	
	FT_lu, FT_u and PC3 IO	$V_{IN} \leq \text{Max}(V_{DDXXX})^{(4)}$	-	-	± 150	
		$\text{Max}(V_{DDXXX}) \leq V_{IN} \leq \text{Max}(V_{DDXXX}) + 1 \text{ V}^{(4)}$	-	-	$2500^{(3)(7)}$	
		$\text{Max}(V_{DDXXX}) + 1 \text{ V} < V_{IN} \leq 5.5 \text{ V}^{(4)(5)(7)}$	-	-	$250^{(7)}$	
	TT_xx input leakage current	$V_{IN} \leq \text{Max}(V_{DDXXX})^{(6)}$	-	-	± 150	
		$\text{Max}(V_{DDXXX}) \leq V_{IN} < 3.6 \text{ V}^{(6)}$	-	-	$2000^{(3)}$	
	OPAMPx_VINM (x=1,2) dedicated input leakage current (UFBGA132 only)	$T_J = 75^\circ\text{C}$	-	-	1	
R_{PU}	Weak pull-up equivalent resistor ⁽⁸⁾	$V_{IN} = V_{SS}$	25	40	55	k Ω
R_{PD}	Weak pull-down equivalent resistor ⁽⁸⁾	$V_{IN} = V_{DDIOx}$	25	40	55	k Ω
C_{IO}	I/O pin capacitance	-	-	5	-	pF

1. Refer to [Figure 22: I/O input characteristics](#).
2. Tested in production.
3. Guaranteed by design.
4. $\text{Max}(V_{DDXXX})$ is the maximum value of all the I/O supplies. Refer to *Table: Legend/Abbreviations used in the pinout table*.
5. All TX_xx IO except FT_lu, FT_u and PC3.
6. This value represents the pad leakage of the IO itself. The total product pad leakage is provided by this formula:
 $I_{\text{Total_leak_max}} = 10 \mu\text{A} + [\text{number of IOs where } V_{IN} \text{ is applied on the pad}] \times I_{lkg}(\text{Max})$.
7. To sustain a voltage higher than $\text{MIN}(V_{DD}, V_{DDA}, V_{DDIO2}, V_{DDUSB}, V_{LCD}) + 0.3 \text{ V}$, the internal Pull-up and Pull-Down resistors must be disabled.
8. Pull-up and pull-down resistors are designed with a true resistance in series with a switchable PMOS/NMOS. This PMOS/NMOS contribution to the series resistance is minimal (~10% order).

Table 63. ADC characteristics^{(1) (2)} (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t_{LATINJ}	Trigger conversion latency Injected channels aborting a regular conversion	CKMODE = 00	2.5	3	3.5	$1/f_{ADC}$
		CKMODE = 01	-	-	3.0	
		CKMODE = 10	-	-	3.25	
		CKMODE = 11	-	-	3.125	
t_s	Sampling time	$f_{ADC} = 80 \text{ MHz}$	0.03125	-	8.00625	μs
		-	2.5	-	640.5	$1/f_{ADC}$
$t_{ADCVREG_STUP}$	ADC voltage regulator start-up time	-	-	-	20	μs
t_{CONV}	Total conversion time (including sampling time)	$f_{ADC} = 80 \text{ MHz}$ Resolution = 12 bits	0.1875	-	8.1625	μs
		Resolution = 12 bits	$t_s + 12.5 \text{ cycles for successive approximation} = 15 \text{ to } 653$			$1/f_{ADC}$
$I_{DDA}(ADC)$	ADC consumption from the V_{DDA} supply	$f_s = 5 \text{ Msps}$	-	730	830	μA
		$f_s = 1 \text{ Msps}$	-	160	220	
		$f_s = 10 \text{ ksps}$	-	16	50	
$I_{DDV_S}(ADC)$	ADC consumption from the V_{REF+} single ended mode	$f_s = 5 \text{ Msps}$	-	130	160	μA
		$f_s = 1 \text{ Msps}$	-	30	40	
		$f_s = 10 \text{ ksps}$	-	0.6	2	
$I_{DDV_D}(ADC)$	ADC consumption from the V_{REF+} differential mode	$f_s = 5 \text{ Msps}$	-	260	310	μA
		$f_s = 1 \text{ Msps}$	-	60	70	
		$f_s = 10 \text{ ksps}$	-	1.3	3	

1. Guaranteed by design
2. The I/O analog switch voltage booster is enable when $V_{DDA} < 2.4 \text{ V}$ (BOOSTEN = 1 in the SYSCFG_CFGR1 when $V_{DDA} < 2.4 \text{ V}$). It is disable when $V_{DDA} \geq 2.4 \text{ V}$.
3. V_{REF+} can be internally connected to V_{DDA} and V_{REF-} can be internally connected to V_{SSA} , depending on the package. Refer to [Section 4: Pinouts and pin description](#) for further details.

Table 68. ADC accuracy - limited test conditions 4⁽¹⁾(2)(3) (continued)

Sym- bol	Parameter	Conditions ⁽⁴⁾			Min	Typ	Max	Unit
THD	Total harmonic distortion	ADC clock frequency \leq 26 MHz, $1.65\text{ V} \leq V_{DDA} = V_{REF+} \leq 3.6\text{ V}$, Voltage scaling Range 2	Single ended	Fast channel (max speed)	-	-71	-69	dB
				Slow channel (max speed)	-	-71	-69	
			Differential	Fast channel (max speed)	-	-73	-72	
				Slow channel (max speed)	-	-73	-72	

1. Guaranteed by design.
2. ADC DC accuracy values are measured after internal calibration.
3. ADC accuracy vs. negative Injection Current: Injecting negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative current.
4. The I/O analog switch voltage booster is enable when $V_{DDA} < 2.4\text{ V}$ (BOOSTEN = 1 in the SYSCFG_CFGR1 when $V_{DDA} < 2.4\text{ V}$). It is disable when $V_{DDA} \geq 2.4\text{ V}$. No oversampling.

6.3.19 Voltage reference buffer characteristics

Table 71. VREFBUF characteristics⁽¹⁾

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DDA}	Analog supply voltage	Normal mode	$V_{RS} = 0$	2.4	-	3.6	V
			$V_{RS} = 1$	2.8	-	3.6	
		Degraded mode ⁽²⁾	$V_{RS} = 0$	1.65	-	2.4	
			$V_{RS} = 1$	1.65	-	2.8	
V_{REFBUF_OUT}	Voltage reference output	Normal mode	$V_{RS} = 0$	2.046 ⁽³⁾	2.048	2.049 ⁽³⁾	
			$V_{RS} = 1$	2.498 ⁽³⁾	2.5	2.502 ⁽³⁾	
		Degraded mode ⁽²⁾	$V_{RS} = 0$	$V_{DDA} - 150 \text{ mV}$	-	V_{DDA}	
			$V_{RS} = 1$	$V_{DDA} - 150 \text{ mV}$	-	V_{DDA}	
TRIM	Trim step resolution	-	-	-	± 0.05	± 0.1	%
CL	Load capacitor	-	-	0.5	1	1.5	μF
esr	Equivalent Serial Resistor of Cloud	-	-	-	-	2	Ω
I_{load}	Static load current	-	-	-	-	4	mA
I_{line_reg}	Line regulation	$2.8 \text{ V} \leq V_{DDA} \leq 3.6 \text{ V}$	$I_{load} = 500 \mu\text{A}$	-	200	1000	ppm/V
			$I_{load} = 4 \text{ mA}$	-	100	500	
I_{load_reg}	Load regulation	$500 \mu\text{A} \leq I_{load} \leq 4 \text{ mA}$	Normal mode	-	50	500	ppm/mA
T_{Coeff}	Temperature coefficient	$-40 \text{ }^\circ\text{C} < T_J < +125 \text{ }^\circ\text{C}$		-	-	$T_{coeff_vrefint} + 50$	ppm/ $^\circ\text{C}$
		$0 \text{ }^\circ\text{C} < T_J < +50 \text{ }^\circ\text{C}$		-	-	$T_{coeff_vrefint} + 50$	
PSRR	Power supply rejection	DC		40	60	-	dB
		100 kHz		25	40	-	
t_{START}	Start-up time	CL = 0.5 μF		-	300	350	μs
		CL = 1.1 μF		-	500	650	
		CL = 1.5 μF		-	650	800	
I_{INRUSH}	Control of maximum DC current drive on VREFBUF_OUT during start-up phase ⁽⁴⁾	-	-	-	8	-	mA

1. Guaranteed by design.
2. LCD enabled with 3 V internal step-up active, 1/8 duty, 1/4 bias, division ratio= 64, all pixels active, no LCD connected.

6.3.25 DFSDM characteristics

Unless otherwise specified, the parameters given in [Table 78](#) for DFSDM are derived from tests performed under the ambient temperature, f_{APB2} frequency and V_{DD} supply voltage conditions summarized in [Table 22: General operating conditions](#).

- Output speed is set to $OSPEEDRy[1:0] = 10$
- Capacitive load $C = 30$ pF
- Measurement points are done at CMOS levels: $0.5 \times V_{DD}$

Refer to [Section 6.3.14: I/O port characteristics](#) for more details on the input/output alternate function characteristics (DFSDM_CKINy, DFSDM_DATINy, DFSDM_CKOUT for DFSDM).

Table 78. DFSDM characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$f_{DFSDMCLK}$	DFSDM clock	-	-	-	f_{SYSCLK}	MHz
f_{CKIN} ($1/T_{CKIN}$)	Input clock frequency	SPI mode (SITP[1:0] = 01)	-	-	20 ($f_{DFSDMCLK}/4$)	
f_{CKOUT}	Output clock frequency	-	-	-	20	MHz
$DuCy_{CKOUT}$	Output clock frequency duty cycle	-	45	50	55	%
$t_{wh(CKIN)}$ $t_{wl(CKIN)}$	Input clock high and low time	SPI mode (SITP[1:0] = 01), External clock mode (SPICKSEL[1:0] = 0)	$T_{CKIN}/2-0.5$	$T_{CKIN}/2$	-	ns
t_{su}	Data input setup time	SPI mode (SITP[1:0]=01), External clock mode (SPICKSEL[1:0] = 0)	0	-	-	
t_h	Data input hold time	SPI mode (SITP[1:0]=01), External clock mode (SPICKSEL[1:0] = 0)	2	-	-	
$T_{Manchester}$	Manchester data period (recovered clock period)	Manchester mode (SITP[1:0] = 10 or 11), Internal clock mode (SPICKSEL[1:0] \neq 0)	$(CKOUT DIV+1) \times T_{DFSDMCLK}$	-	$(2 \times CKOUTDIV) \times T_{DFSDMCLK}$	

1. Data based on characterization results, not tested in production.

6.3.27 Communication interfaces characteristics

I²C interface characteristics

The I2C interface meets the timings requirements of the I²C-bus specification and user manual rev. 03 for:

- Standard-mode (Sm): with a bit rate up to 100 kbit/s
- Fast-mode (Fm): with a bit rate up to 400 kbit/s
- Fast-mode Plus (Fm+): with a bit rate up to 1 Mbit/s.

The I2C timings requirements are guaranteed by design when the I2C peripheral is properly configured (refer to RM0351 reference manual).

The SDA and SCL I/O requirements are met with the following restrictions: the SDA and SCL I/O pins are not “true” open-drain. When configured as open-drain, the PMOS connected between the I/O pin and V_{DDIOx} is disabled, but is still present. Only FT_f I/O pins support Fm+ low level output current maximum requirement. Refer to [Section 6.3.14: I/O port characteristics](#) for the I2C I/Os characteristics.

All I2C SDA and SCL I/Os embed an analog filter. Refer to the table below for the analog filter characteristics:

Table 82. I2C analog filter characteristics⁽¹⁾

Symbol	Parameter	Min	Max	Unit
t _{AF}	Maximum pulse width of spikes that are suppressed by the analog filter	50 ⁽²⁾	260 ⁽³⁾	ns

1. Guaranteed by design.
2. Spikes with widths below t_{AF(min)} are filtered.
3. Spikes with widths above t_{AF(max)} are not filtered

Table 99. Synchronous multiplexed PSRAM write timings⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
$t_{w(CLK)}$	FMC_CLK period	$2T_{HCLK}-1$	-	ns
$t_{d(CLKL-NExL)}$	FMC_CLK low to FMC_NEx low ($x=0..2$)	-	2	
$t_{d(CLKH-NExH)}$	FMC_CLK high to FMC_NEx high ($x=0..2$)	$T_{HCLK}+0.5$	-	
$t_{d(CLKL-NADV_L)}$	FMC_CLK low to FMC_NADV low	-	2.5	
$t_{d(CLKL-NADV_H)}$	FMC_CLK low to FMC_NADV high	1	-	
$t_{d(CLKL-AV)}$	FMC_CLK low to FMC_Ax valid ($x=16..25$)	-	3.5	
$t_{d(CLKH-AIV)}$	FMC_CLK high to FMC_Ax invalid ($x=16..25$)	T_{HCLK}	-	
$t_{d(CLKL-NWEL)}$	FMC_CLK low to FMC_NWE low	-	2	
$t_{d(CLKH-NWEH)}$	FMC_CLK high to FMC_NWE high	$T_{HCLK}+1$	-	
$t_{d(CLKL-ADV)}$	FMC_CLK low to FMC_AD[15:0] valid	-	4	
$t_{d(CLKL-ADIV)}$	FMC_CLK low to FMC_AD[15:0] invalid	0	-	
$t_{d(CLKL-DATA)}$	FMC_A/D[15:0] valid data after FMC_CLK low	-	5.5	
$t_{d(CLKL-NBLL)}$	FMC_CLK low to FMC_NBL low	-	2.5	
$t_{d(CLKH-NBLH)}$	FMC_CLK high to FMC_NBL high	$T_{HCLK}+1$	-	
$t_{su(NWAIT-CLKH)}$	FMC_NWAIT valid before FMC_CLK high	0	-	
$t_h(CLKH-NWAIT)$	FMC_NWAIT valid after FMC_CLK high	4	-	

1. CL = 30 pF.

2. Guaranteed by characterization results.

Table 105. UFBGA132 - 132-ball, 7 x 7 mm ultra thin fine pitch ball grid array package mechanical data (continued)

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
e	-	0.500	-	-	0.0197	-
Z	-	0.750	-	-	0.0295	-
ddd	-	0.080	-	-	0.0031	-
eee	-	0.150	-	-	0.0059	-
fff	-	0.050	-	-	0.0020	-

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 53. UFBGA132 - 132-ball, 7 x 7 mm ultra thin fine pitch ball grid array package recommended footprint

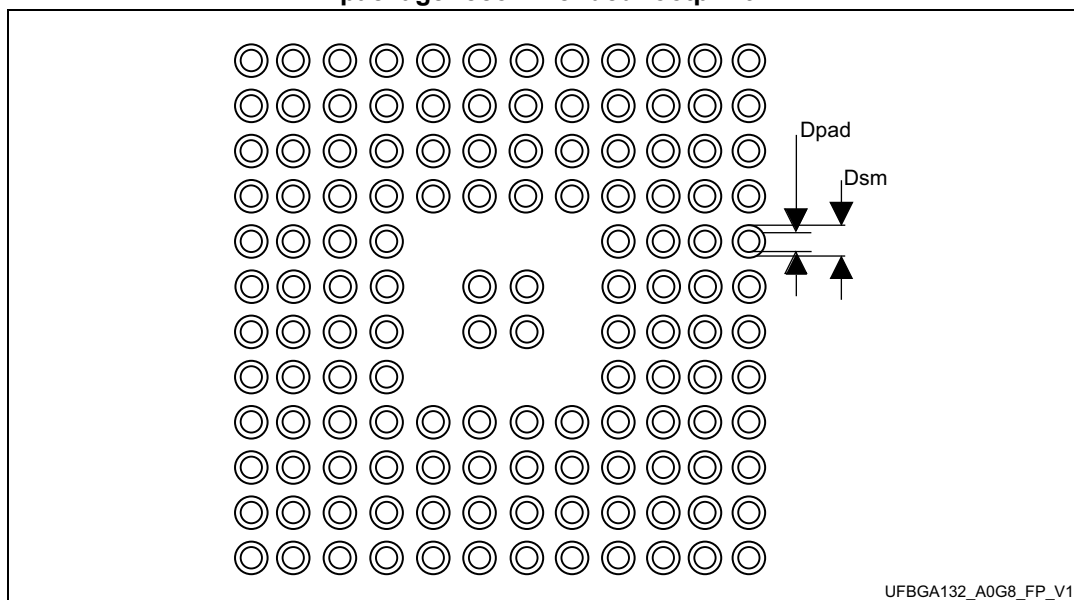


Table 106. UFBGA132 recommended PCB design rules (0.5 mm pitch BGA)

Dimension	Recommended values
Pitch	0.5 mm
Dpad	0.280 mm
Dsm	0.370 mm typ. (depends on the soldermask registration tolerance)
Stencil opening	0.280 mm
Stencil thickness	Between 0.100 mm and 0.125 mm
Pad trace width	0.100 mm
Ball diameter	0.280 mm